PD -2.362A

International
IOR Rectifier

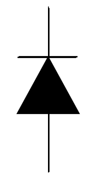
HFA12PA120C

HEXFRED™

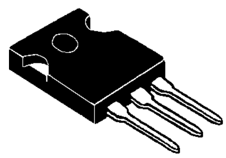
Ultrafast, Soft Recovery Diode

Features
- Ultrafast Recovery
- Ultrasoft Recovery
- Very Low I_{RRM}
- Very Low Q_{rr}
- Guaranteed Avalanche
- Specified at Operating Conditions

Benefits
- Reduced RFI and EMI
- Reduced Power Loss in Diode and Switching Transistor
- Higher Frequency Operation
- Reduced Snubbing
- Reduced Parts Count



V_R = 1200V
V_F(typ.)* = 2.4V
$I_{F(AV)}$ = 6A
Q_{rr} (typ.)= 116nC
I_{RRM}(typ.) = 4.4A
t_{rr}(typ.) = 26ns
$di_{(rec)M}/dt$ (typ.)* = 100A/µs



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Description
International Rectifier's HFA12PA120C is a state of the art center tap ultra fast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which results in performance which is unsurpassed by any rectifier previously available. The HFA12PA120C has basic ratings of 1200 volts and 6 amps per leg continuous current. In addition to ultra fast recovery time, the HEXFRED product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA12PA120C is ideally suited for applications in power supplies and power conversion systems (such as inverters, converters, UPS systems, and power factor correction circuits), motor drives, and many other similar applications where high speed, high efficiency is needed.

Absolute Maximum Ratings

	Parameter	Max.	Units
V_R	Cathode-to-Anode Voltage	1200	V
I_F @ T_C = 25°C	Continuous Forward Current		A
I_F @ T_C = 100°C	Continuous Forward Current	6.0	
I_{FSM}	Single Pulse Forward Current	80	
I_{FRM}	Maximum Repetitive Forward Current	24	
I_{AS}①	Maximum Single Pulse Avalanche Current	6.0	
P_D @ T_C = 25°C	Maximum Power Dissipation	62.5	W
P_D @ T_C = 100°C	Maximum Power Dissipation	25	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C

* 125°C

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions	
V_{BR}	Cathode Anode Breakdown Voltage	1200	–––	–––	V	I_R = 100µA	
V_{FM}	Max Forward Voltage	–––	2.7	3.0	V	I_F = 6A	See Fig. 1
		–––	3.5	3.9		I_F = 12A	
		–––	2.4	2.8		I_F = 6A, T_J = 125°C	
I_{RM}	Max Reverse Leakage Current	–––	0.26	5.0	µA	V_R = V_R Rated	See Fig. 2
		–––	110	500		T_J = 125°C, V_R = 0.8 x V_R Rated	
C_T	Junction Capacitance	–––	9.0	14	pF	V_R = 200V	See Fig. 3
L_S	Series Inductance	–––	12	–––	nH	Measured lead to lead 5mm from package body	

Dynamic Recovery Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions	
t_{rr}	Reverse Recovery Time	–––	26	–––	ns	I_F = 1.0A, di_f/dt = 200A/µs, V_R = 30V	
t_{rr1}	See Fig. 5, 10	–––	53	80		T_J = 25°C	
t_{rr2}		–––	87	130		T_J = 125°C	I_F = 6A
I_{RRM1}	Peak Recovery Current	–––	4.4	8.0	A	T_J = 25°C	
I_{RRM2}	See Fig. 6	–––	5.0	9.0		T_J = 125°C	V_R = 200V
Q_{rr1}	Reverse Recovery Charge	–––	116	320	nC	T_J = 25°C	
Q_{rr2}	See Fig. 7	–––	233	585		T_J = 125°C	di_f/dt = 200A/µs
$di_{(rec)M}/dt1$	Peak Rate of Fall of Recovery Current	–––	180	–––	A/µs	T_J = 25°C	
$di_{(rec)M}/dt2$	During t_b See Fig. 8	–––	100	–––		T_J = 125°C	

Thermal - Mechanical Characteristics

	Parameter	Min.	Typ.	Max.	Units
T_{lead}②	Lead Temperature	––––	––––	300	°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	––––	––––	2.0	K/W
		––––	––––	1.0	
$R_{\theta JA}$③	Thermal Resistance, Junction to Ambient	––––	––––	40	
$R_{\theta CS}$④	Thermal Resistance, Case to Heat Sink	––––	0.25	––––	
Wt	Weight	––––	6.0	––––	g
		––––	0.21	––––	(oz)
	Mounting Torque	6.0	––––	12	Kg-cm
		5.0	––––	10	lbf•in

① L=100µH, duty cycle limited by max T_J

② 0.063 in. from Case (1.6mm) for 10 sec

③ Typical Socket Mount

④ Mounting Surface, Flat, Smooth and Greased

Instantaneous Forward Current - I_F (A)

Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

Reverse Current - I_R (µA)

Fig. 2 - Typical Reverse Current vs. Reverse Voltage

Junction Capacitance -C_T (pF)

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

Fig. 4 - Maximum Thermal Impedance Z_{thjc} Characteristics

trr- (nC)

Irr- (A)

Fig. 5 - Typical Reverse Recovery vs. di_f/dt, (per Leg)

Fig. 6 - Typical Recovery Current vs. di_f/dt, (per Leg)

Qrr- (nC)

di (rec) M/dt- (A /µs)

Fig. 7 - Typical Stored Charge vs. di_f/dt, (per Leg)

Fig. 8 - Typical $di_{(rec)M}/dt$ vs. di_f/dt, (per Leg)

REVERSE RECOVERY CIRCUIT

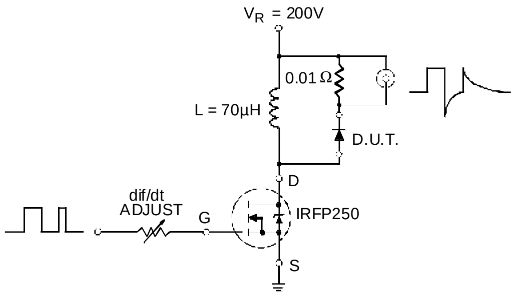
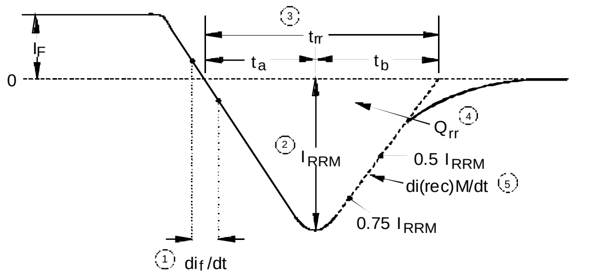


Fig. 9 - Reverse Recovery Parameter Test Circuit



1. di_f/dt - Rate of change of current through zero crossing
2. I_{RRM} - Peak reverse recovery current
3. trr - Reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current
4. Q_{rr} - Area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

5. $di_{(rec)M}/dt$ - Peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

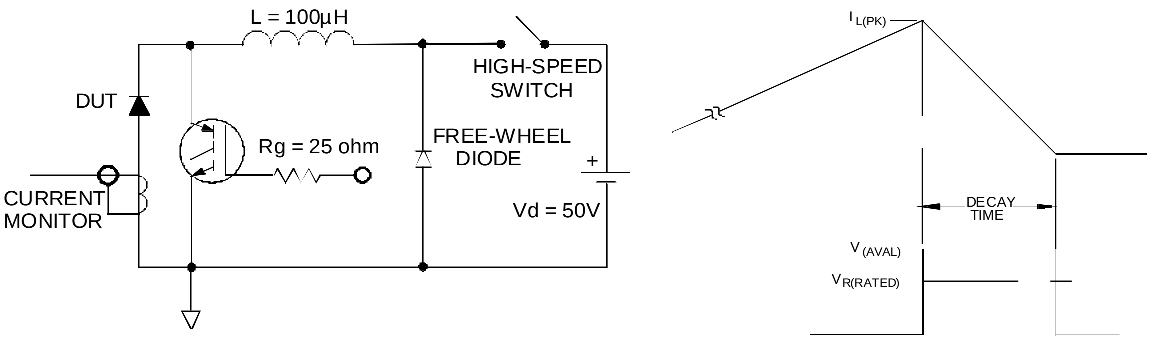
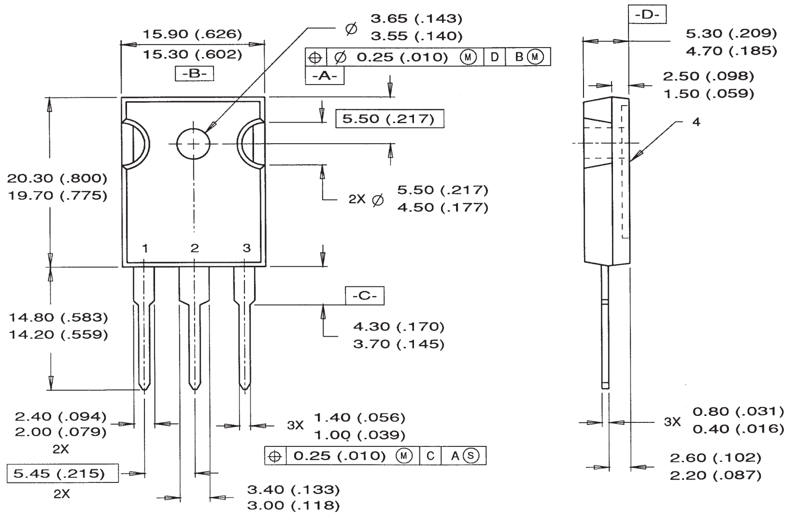


Fig. 11 - Avalanche Test Circuit and Waveforms



Conforms to JEDEC Outline TO-247AC
Dimensions in millimeters and inches

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